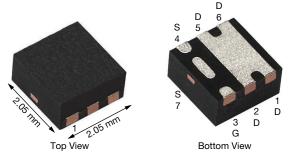
www.vishay.com

Vishay Siliconix

P-Channel 30 V (D-S) MOSFET

PowerPAK[®] SC-70-6L Single



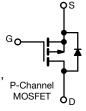
 $\begin{tabular}{|c|c|c|c|} \hline PRODUCT SUMMARY \\ \hline V_{DS} (V) & -30 \\ \hline R_{DS(on)} \max. (\Omega) \mbox{ at } V_{GS} = -10 \ V & 0.0140 \\ \hline R_{DS(on)} \max. (\Omega) \mbox{ at } V_{GS} = -4.5 \ V & 0.0241 \\ \hline Q_g \mbox{ typ. (nC)} & 8.9 \\ \hline I_D (A) & -30.3 \\ \hline Configuration & Single \\ \hline \end{tabular}$

FEATURES

- TrenchFET[®] Gen IV p-channel power MOSFET
- Thermally enhanced PowerPAK[®] SC-70 package RoHS
- Very low R_{DS(on)} x area minimizes power loss on limited PCB real estate
- Provides excellent R_{DS}-Q_g Figure-of-Merit (FOM) for switching applications
- 100 % R_a tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

- · Battery charging and management
- Load switch
- DC/DC converters
- Power management in battery-operated, mobile and wearable devices



Marking code: B9

ORDERING INFORMATION	
Package	PowerPAK SC-70
Lead (Pb)-free and halogen-free	SiA471DJ-T1-GE3

PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V _{DS}	-30	N	
Gate-source voltage		V _{GS}	-20 / +16	V	
Continuous drain current (T _J = 150 °C)	T _C = 25 °C		-30.3		
	T _C = 70 °C		-24.2		
	T _A =25 °C	I _D	-12.9 ^{a, b}		
	T _A = 70 °C	1	-10.3 ^{a, b}	А	
Pulsed drain current (t = 100 μs)		I _{DM}	-70		
Continuous source-drain diode current	T _C = 25 °C		-16		
	T _A = 25 °C	I _S	-2.9 ^{a, b}		
Maximum power dissipation	T _C = 25 °C		19.2		
	T _C = 70 °C		12.3	14/	
	T _A = 25 °C	P _D	3.5 ^{a, b}	W	
	T _A = 70 °C	1	2.2 ^{a, b}		
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +150	°C	
Soldering recommendations (peak temperature) c, d		Ĭ	260		

THERMAL RESISTANCE RATINGS

PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT		
Maximum junction-to-ambient a, e	t ≤ 5 s	R _{thJA}	28	36	°C/W		
Maximum junction-to-case (drain)	Steady state	R _{thJC}	5.3	6.5	- '0/w		

Notes

a. Surface mounted on 1" x 1" FR4 board

b. t = 5 s

c. See solder profile (<u>www.vishay.com/ppg?73257</u>). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection

d. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

e. Maximum under steady state conditions is 80 °C/W

S19-0336-Rev. B, 08-Apr-2019

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For technical questions, contact: pmostechsupport@vishay.com

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HALOGEN

FREE

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Vishay Siliconix

SiA471DJ

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static			•		•		
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0 \text{ V}, \text{ I}_{D} = -250 \mu\text{A}$	-30	-	-	V	
V _{DS} temperature coefficient	$\Delta V_{DS}/T_{J}$		-	-15	-	mV/°C	
V _{GS(th)} temperature coefficient	$\Delta V_{GS(th)}/T_J$	I _D = -10 mA	-	5	-		
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = -250 \ \mu A$	-1	-	-2.5	V	
Gate-source leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, \text{ V}_{GS} = -20 \text{ V} / +16 \text{ V}$	-	-	± 100	nA	
Zero gate voltage drain current	I _{DSS}	$V_{DS} = -30 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	-	-	-1		
		V_{DS} = -30 V, V_{GS} = 0 V, T_{J} = 55 °C	-	-	-10	μA	
On-state drain current ^a	I _{D(on)}	$V_{DS} \le$ -5 V, V_{GS} = 0 V	-10	-	-	А	
Drain-source on-state resistance ^a	D	$V_{GS} = -10 \text{ V}, \text{ I}_{D} = -10 \text{ A}$	-	0.0115	0.0140	Ω	
	R _{DS(on)}	$V_{GS} = -4.5 \text{ V}, \text{ I}_{D} = -7 \text{ A}$	-	0.0185	0.0241		
Forward transconductance a	9 _{fs}	$V_{DS} = -10 \text{ V}, \text{ I}_{D} = -10 \text{ A}$	-	40	-	S	
Dynamic ^b			•		•		
Input capacitance	C _{iss}	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, \text{ f} = 1 \text{ MHz}$	-	1170	-	pF	
Output capacitance	C _{oss}		-	570	-		
Reverse transfer capacitance	C _{rss}		-	55	-		
	Q _g	$V_{DS} = -15 \text{ V}, \text{ V}_{GS} = -10 \text{ V}, \text{ I}_{D} = -12 \text{ A}$	-	18.5	27.8		
Total gate charge		V_{DS} = -15 V, V_{GS} = -4.5 V, I_{D} = -12 A	-	8.9	14	nC	
Gate-source charge	Q _{gs}		-	4.4	-		
Gate-drain charge	Q _{gd}	V_{DS} = -15 V, V_{GS} = -4.5 V, I_D = -12 A	-	2.7	-		
Gate resistance	Rg	f = 1 MHz	0.22	11	22	Ω	
Turn-on delay time	t _{d(on)}		-	25	50	-	
Rise time	t _r	$\label{eq:VDD} \begin{array}{l} V_{\text{DD}} = \text{-15 V}, \ R_{\text{L}} = \text{1.5 }\Omega, \ I_{\text{D}} \cong \text{-10 A}, \\ V_{\text{GEN}} = \text{-4.5 V}, \ R_{\text{g}} = \text{1} \ \Omega \end{array}$	-	95	190		
Turn-off delay time	t _{d(off)}		-	40	80		
Fall time	t _f		-	18	36		
Turn-on delay time	t _{d(on)}		-	13	26	- ns -	
Rise time	t _r	$V_{DD} = -15 \text{ V}, \text{ R}_{L} = 1.5 \Omega, \text{ I}_{D} \cong -10 \text{ A},$	-	8	16		
Turn-off delay time	t _{d(off)}	V_{GEN} = -10 V, R_g = 1 Ω	-	35	70		
Fall time	t _f		-	15	30		
Drain-Source Body Diode Characterist	ics			•			
Continuous source-drain diode current	I _S	T _C = 25 °C	-	-	-16		
Pulse diode forward current	I _{SM}		-	-	-70	— A	
Body diode voltage	V _{SD}	I _S = -10 A, V _{GS} = 0 V	-	-0.85	-1.2	V	
Body diode reverse recovery time	t _{rr}		-	21	42	ns	
Body diode reverse recovery charge	Q _{rr}	I _F = -10 A, di/dt = 100 A/μs, T _J = 25 °C	-	8	16	nC	
Reverse recovery fall time	ta		-	9	-	ns	
Reverse recovery rise time	t _b		-	12	-		

Notes

a. Pulse test; pulse width $\leq 300~\mu\text{s},~\text{duty}~\text{cycle} \leq 2~\%$

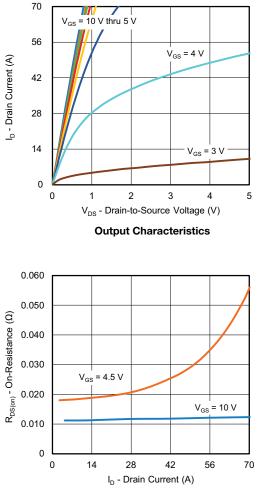
b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

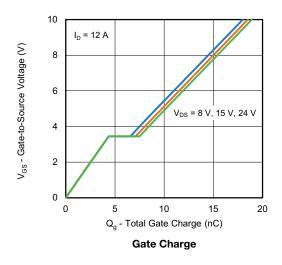
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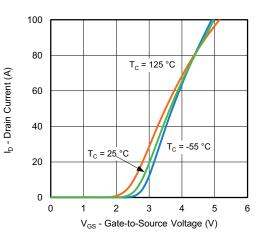


TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

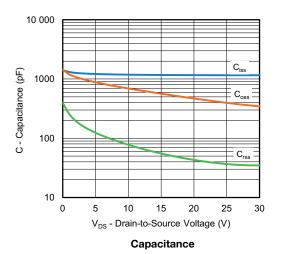


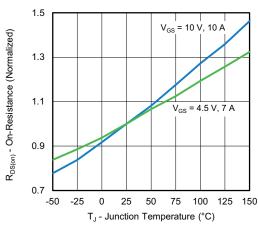
On-Resistance vs. Drain Current and Gate Voltage





Transfer Characteristics



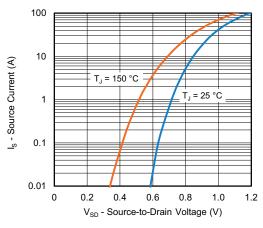


On-Resistance vs. Junction Temperature

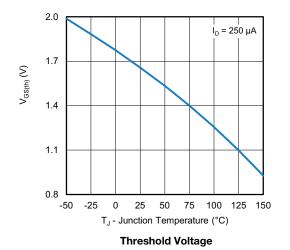
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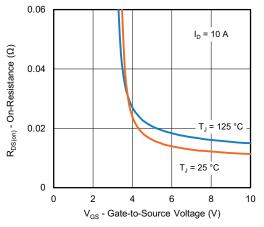


TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

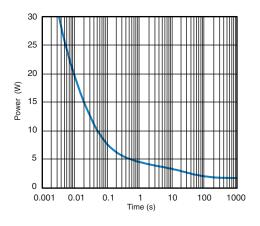


Source-Drain Diode Forward Voltage

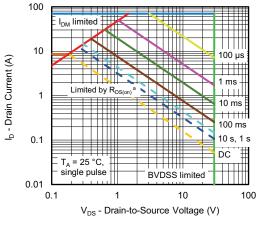




On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power, Junction-to-Ambient



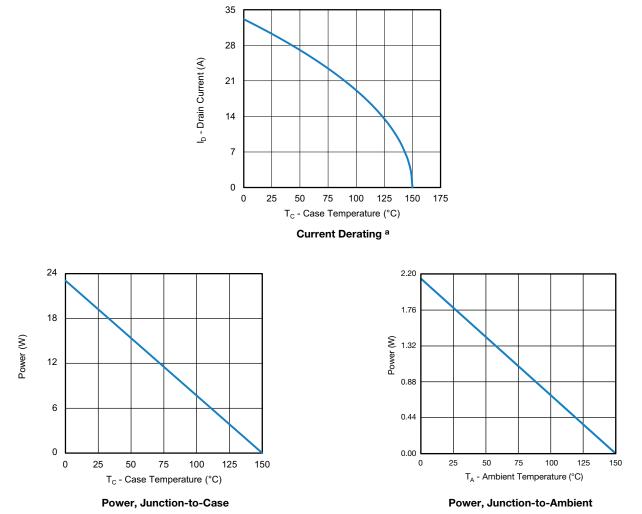
Safe Operating Area, Junction-to-Ambient

Note

a. V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

4

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

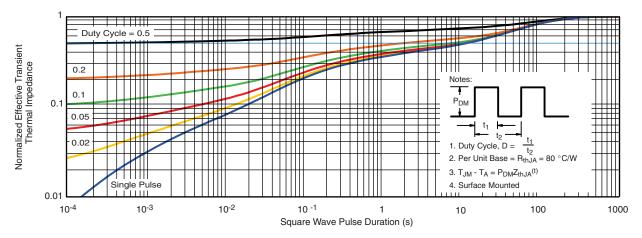


Note

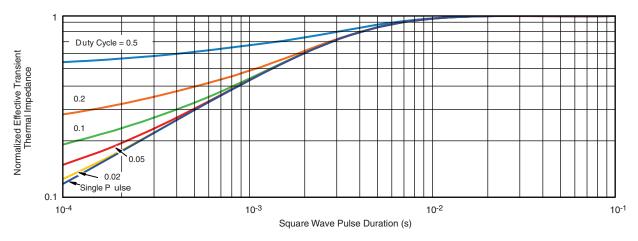
a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-ambient thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?76741.



PowerPAK[®] SC70-6L

VISHA

b PIN2 PIN1 PIN3 _ ₹



b

PIN3

__ ₿

PIN2

PIN1

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RECOMMENDED PAD LAYOUT FOR PowerPAK[®] SC70-6L Single



Dimensions in mm/(Inches)

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